





## NPN SILICON PLANAR EPITAXIAL TRANSISTOR

**BF959** 



TO-92 Plastic Package RoHS compliant

TO-92

## **GENERAL DESCRIPTION:**

BF 959 IS A SILICON NPN TRANSISTOR INTENDED FOR USE AT VERY HIGH FREQUENCIES.

**ABSOLUTE MAXIMUM RATINGS** (Ta = 25 °C Unless otherwise specified)

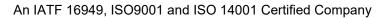
PARAMETER	SYMBOL	VALUE	UNIT
Collector Emitter Voltage	$V_{CEO}$	20	V
Collector Base Voltage	$V_{CBO}$	30	V
Emitter Base Voltage	$V_{EBO}$	3	V
Collector Current Continuous	I <sub>C</sub>	100	mA
Power Dissipation @ T <sub>a</sub> =25°C	D	625	mW
Derate Above 25°C	$P_{D}$	5.0	mW/°C
Power Dissipation @ T <sub>c</sub> =25°C	0	1.5	W
Derate Above 25°C	$P_{D}$	12	mW/°C
Operating And Storage Junction Temperature Range	$T_{j},T_{stg}$	-55 to +150	°C

## THERMAL RESISTANCE

Thermal Resistance, Junction-to-Ambient	$R_{th(j-a)}$	200	°C/W
Thermal Resistance, Junction to case	$R_{th(j-c)}$	83.3	°C/W



## Continental Device India Pvt. Limited







**ELECTRICAL CHARACTERISTICS at** (Ta = 25 °C Unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITION	,	UNIT		
PARAMETER	STIVIBUL	TEST CONDITION	MIN	TYP	MAX	UNII
Collector Emitter Breakdown Voltage	BV <sub>CEO</sub>	$I_C=1mA,I_B=0$	20			V
Collector Base Breakdown Voltage	$BV_{CBO}$	$I_{C}=10\mu A, I_{E}=0$	30			V
Emitter Base Breakdown Voltage	$BV_{EBO}$	$I_E=10\mu A, I_C=0$	3			V
Collector Cut off Current	I <sub>CBO</sub>	$V_{CB} = 20V, I_{E} = 0$			100	nA
DC Current Gain	h	$V_{CE}$ =10V, $I_{C}$ =5mA	35			
Current Gain	h <sub>FE</sub>	$V_{CE}$ =10V, $I_{C}$ =20mA	40	ŀ		
Base Emitter Saturation Voltage	$V_{BE(sat)}$	I <sub>C</sub> =30mA,I <sub>B</sub> =2mA	1	ŀ	1.0	V
Collector Emitter Saturation Voltage	$V_{CE(sat)}$	I <sub>C</sub> =30mA,I <sub>B</sub> =2mA	1	ŀ	1.0	V

## **DYNAMIC CHARACTERSTICS**

Transition Fraguency	f	I <sub>C</sub> =20mA, V <sub>CE</sub> =10V, f=100MHz				MHz
Transition Frequency	† <sub>T</sub>	$I_C$ =30mA, $V_{CE}$ =10V, f=100MHz	600	-		MHz
Common Emitter Feedback Capacitance	$C_{re}$	V <sub>CB</sub> =10V, f=10MHz	I	0.65	I	pF
Noise Figure	NF	$I_C$ =4mA, $V_{CE}$ =10V, Rs=50 $\Omega$ , f=200MHz	1	3.0	1	dB

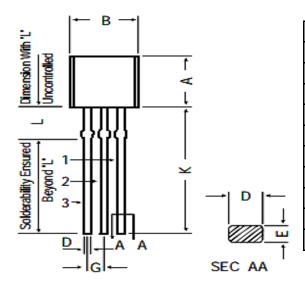




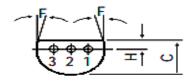


# **PACKAGE DETAILS**

TO-92 Plastic Package



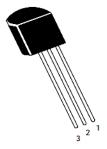
MIN	MAX
4.32	5.33
4.45	5.20
3.18	4.19
0.41	0.55
0.35	0.50
5°	
1.14	1.40
1.14	1.53
12.70	
1.982	2.082
	4.32 4.45 3.18 0.41 0.35 5° 1.14 1.14 12.70



All dimensions in mm.

## **Pin Configuration**

- 1. Base
- 2. Emitter
- 3. Collector

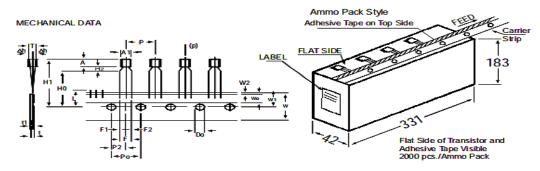








## **TO-92 Transistors on Tape and Ammo Pack**



All dimensions in mm unless specified otherwise

17514			SPECIFICATION			
ITEM	SYMBOL	MIN.	NOM.	MAX.	TOL .	REMARKS
BODY WIDTH	A1	4.0		4.8		
BODY HEIGHT	Α	4.8		5.2		
BODY THICKNESS	Ţ	3.9		4.2	_	
PITCH OF COMPONENT	Р		12.7 12.7		±1	
FEED HOLE PITCH	Po		12.7		±0.3	CUMULATIVE PITCH ERROR 1.0 mm/20 PITCH
FEED HOLE CENTRE TO			/ OF			
COMPONENT CENTRE	P2		6.35		±0.4	TO BE MEASURED AT BOTTOM OF CLINCH
DISTANCE BETWEEN OUTER					+0.6	
LEADS	F		5.08		-0.2	
COMPONENT ALIGNMENT	Δh		0	1		AT TOP OF BODY
TAPE WIDTH HOLD-DOWN TAPE WIDTH	W		18		±0.5 ±0.2	
HOLD-DOWN TAPE WIDTH	Wo W1		6		+0.7	
HOLE POSITION	WI		7		-0.5	
HOLD-DOWN TAPE POSITION	W2		0.5		±0.2	
LEAD WIRE CLINCH HEIGHT	Ho		16		±0.5	
COMPONENT HEIGHT	H1			23.25		
LENGTH OF SNIPPED LEADS	L			11.0		
FEED HOLE DIAMETER	Do		4		±0.2	
TOTAL TAPE THICKNESS	t		0.54	1.2	l l	t1 0.3 - 0.6
LEAD - TO - LEAD DISTANCEF1,	F2		2.54		+0.4	
CLINCH HEIGHT	H2			3		
PULL - OUT FORCE	(P)	6N				

#### Notes:

- 1. Maximum Alignment Deviation Between Leads Not to be Greater Than 0.2 mm
- 2. Maximum Non-Cumulative Variation Between Tape Feed Holes Shall not Exceed 1 mm in 20 Pitches.
- 3. Hoedown Tape not to Exceed Beyond the Edge(S) of Carrier Tape & There Shall be no Exposure of Adhesive.
- 4. No More Than 3 Consecutive Missing Components are Permitted.
- 5. A Tape Trailer, Having at least Three Feed Holes are Required After the Last Component.
- 6. Splices Shall not Interfere with the Sprocket Feed Holes.

### **Packing Detail**

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt
TO-92 Bulk TO-92 T&A	' ' '		3" x 7.5" x 7.5" 12.5" x 8" x 1.8"	5K 2K	17" x 15" x 13.5" 17" x 15" x 13.5"	80K 32K	23 kgs 12.5 kgs

BF959

Rev01 29032022E





# Recommended Product Storage Environment for Discrete Semiconductor Devices

This storage environment assumes that the Diodes and transistors are packed properly inside the original packing supplied by CDIL.

- · Temperature 5 °C to 30 °C
- · Humidity between 40 to 70 %RH
- · Air should be clean.
- · Avoid harmful gas or dust.
- · Avoid outdoor exposure or storage in areas subject to rain or water spraying .
- · Avoid storage in areas subject to corrosive gas or dust. Product shall not be stored in areas exposed to direct sunlight.
- · Avoid rapid change of temperature.
- · Avoid condensation.
- · Mechanical stress such as vibration and impact shall be avoided.
- · The product shall not be placed directly on the floor.
- The product shall be stored on a plane area. They should not be turned upside down. They should not be placed against the wall.

#### **Shelf Life of CDIL Products**

The shelf life of products is the period from product manufacture to shipment to customers. The product can be unconditionally shipped within this period. The period is defined as 2 years.

If products are stored longer than the shelf life of 2 years the products shall be subjected to quality check as per CDIL quality procedure.

The products are further warranted for another one year after the date of shipment subject to the above conditions in CDIL original packing.

#### Floor Life of CDIL Products and MSL Level

When the products are opened from the original packing, the floor life will start.

For this, the following JEDEC table may be referred:

JEDEC MSL Level					
Level	Time	Condition			
1	Unlimited	≤30 °C / 85% RH			
2	1 Year	≤30 °C / 60% RH			
2a	4 Weeks	≤30 °C / 60% RH			
3	168 Hours	≤30 °C / 60% RH			
4	72 Hours	≤30 °C / 60% RH			
5	48 Hours	≤30 °C / 60% RH			
5a	24 Hours	≤30 °C / 60% RH			
6	Time on Label(TOL)	≤30 °C / 60% RH			







#### **Customer Notes**

#### **Component Disposal Instructions**

- 1. CDIL Semiconductor Devices are RoHS compliant, customers are requested to please dispose as per prevailing Environmental Legislation of their Country.
- 2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).

#### **Disclaimer**

The product information and the selection guides facilitate selection of the CDIL's Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished in the Data Sheet and on the CDIL Web Site/CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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